

Preliminary datasheet

Short circuit rugged 750 V EDT2 IGBT in reflow-solderable package co-packed with soft and fast recovery diode

Features

- $V_{CE} = 750\text{ V}$
- $I_C = 200\text{ A}$
- Suitable for 470 V V_{DC} systems and increase overvoltage margin for 400 V V_{DC} systems
- Very low $V_{CEsat} = 1.4\text{ V}$ (typ.) at $I_{Cnom} = 200\text{ A}$, 25°C
- Short circuit robust $t_{sc} = 5\text{ }\mu\text{s}$ at $V_{CE} = 470\text{ V}$, $V_{GE} = 15\text{ V}$
- Up to 40% less System R_{th} due to reflow capability, increased power output
- Self limiting current under short circuit condition
- Positive thermal coefficient and very tight parameter distribution for easy paralleling
- A Reduced number of parallel devices is required due to $I_{nom} = 200\text{ A}$
- Excellent current sharing in parallel operation
- Smooth switching characteristics
- Low gate charge Q_G
- Simple gate drive design
- Co-packed with fast soft recovery emitter controlled 3 diode
- Low EMI signature
- TO247PLUS package with high creepage distance
- High reliability and operating lifetime
- Resistive weldable pins for direct busbar connections
- Drop-in replacement for $I_C = 200\text{ A}$, $T_c = 100^\circ\text{C}$ devices



Lead-free



Green



Halogen-free



RoHS

AEC-Q101
Qualified

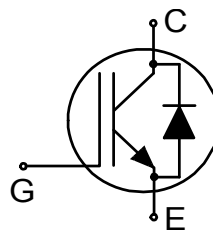
Potential applications

- xEV traction inverter
- DC-link discharge switch
- Automotive aux-drives

Product validation

- Qualified for automotive applications. Product Validation according to AEC-Q101
- Qualified Reflow device according to JEDEC J-STA-020 MSL2

Description



Type	Package	Marking
AIQRB200N75CP2	PG-TO247-3-PLUS-NN8.5	AKQB20FCP

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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	reflow soldering (MSL2 according to JEDEC J-STA-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.12	0.16	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.23	0.3	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$	750	V
DC collector current, limited by T_{vjmax}	I_C	$T_c = 25\text{ °C}$	250	A
		$T_c = 100\text{ °C}$	200	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}		600	A
Turn-off safe operating area		$V_{CE} \leq 750\text{ V}, T_{vj} \leq 175\text{ °C}$	600	A
Gate-emitter voltage	V_{GE}		± 20	V
Transient gate-emitter voltage	V_{GE}	$t_p = 10\text{ }\mu\text{s}, D < 0.01$	± 30	V
Short-circuit withstand time	t_{SC}	$V_{CC} \leq 470\text{ V}, V_{GE} = -8/15\text{ V}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}, T_{vj} = 25\text{ °C}$	5	μs
Power dissipation	P_{tot}	$T_{vj} = 175\text{ °C}$	$T_c = 25\text{ °C}$	W
			$T_c = 100\text{ °C}$	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 200 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.4	1.65	V
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.7		
Gate-emitter threshold voltage	V_{GETh}	$I_C = 2.6 \text{ mA}, V_{CE} = V_{GE}$		5	5.75	6.5	V
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 750 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			200	μA
			$T_{vj} = 175 \text{ }^\circ\text{C}$		5		mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$				100	nA
Transconductance	g_{fs}	$I_C = 200 \text{ A}, V_{CE} = 20 \text{ V}$			140		S
Short-circuit collector current	I_{SC}	$V_{CC} \leq 470 \text{ V}, V_{GE} = -8/15 \text{ V}, t_{SC} \leq 5 \text{ } \mu\text{s}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0 \text{ s}$, $T_{vj} = 25 \text{ }^\circ\text{C}$			1250		A
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$			21250		pF
Output capacitance	C_{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$			535		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$			93		pF
Gate charge	Q_G	$V_{CC} = 600 \text{ V}, I_C = 200 \text{ A}, V_{GE} = -8/15 \text{ V}$			1256		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \text{ } \Omega, R_{G(off)} = 5 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		89		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		85		
Rise time (inductive load)	t_r	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \text{ } \Omega, R_{G(off)} = 5 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		120		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		117		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \text{ } \Omega, R_{G(off)} = 5 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		266		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		284		
Fall time (inductive load)	t_f	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \text{ } \Omega, R_{G(off)} = 5 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		46		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		60		
Turn-on energy ¹⁾	E_{on}	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \text{ } \Omega, R_{G(off)} = 5 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		15.3		mJ
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		16.3		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy	E_{off}	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \Omega, R_{G(off)} = 5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		7	mJ
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		8.1	
Total switching energy	E_{ts}	$V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \Omega, R_{G(off)} = 5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		22.3	mJ
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 200 \text{ A}$		24.4	
Operating junction temperature	T_{vj}		-40		175	$^\circ\text{C}$

1) includes reverse recovery losses

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Diode forward current, limited by T_{vjmax}	I_F		$T_c = 25 \text{ }^\circ\text{C}$	250	A
			$T_c = 100 \text{ }^\circ\text{C}$	200	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}		600	A	
Power dissipation	P_{tot}	$T_{vj} = 175 \text{ }^\circ\text{C}$	$T_c = 25 \text{ }^\circ\text{C}$	500	W
			$T_c = 100 \text{ }^\circ\text{C}$	250	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode forward voltage	V_F	$I_F = 200 \text{ A}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.9	2	V
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.9		
Diode reverse recovery charge	Q_{rr}	$V_R = 470 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_F = 200 \text{ A}, -di_F/dt = 1060 \text{ A}/\mu\text{s}$		4.7		μC
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_F = 200 \text{ A}, -di_F/dt = 1110 \text{ A}/\mu\text{s}$		7.5		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode peak reverse recovery current	I_{rrm}	$V_R = 470 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$, $I_F = 200 \text{ A}$, $-di_F/dt = 1060 \text{ A}/\mu\text{s}$		41		A
			$T_{vj} = 175 \text{ }^\circ\text{C}$, $I_F = 200 \text{ A}$, $-di_F/dt = 1110 \text{ A}/\mu\text{s}$		56		
Reverse recovery energy	E_{rec}	$V_R = 470 \text{ V}$, $L_\sigma = 50 \text{ nH}$, $C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}$, $I_F = 200 \text{ A}$, $-di_F/dt = 1060 \text{ A}/\mu\text{s}$		1.3		mJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$, $I_F = 200 \text{ A}$, $-di_F/dt = 1110 \text{ A}/\mu\text{s}$		2.2		
Operating junction temperature	T_{vj}			-40		175	$^\circ\text{C}$

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Electrical Characteristic at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified.

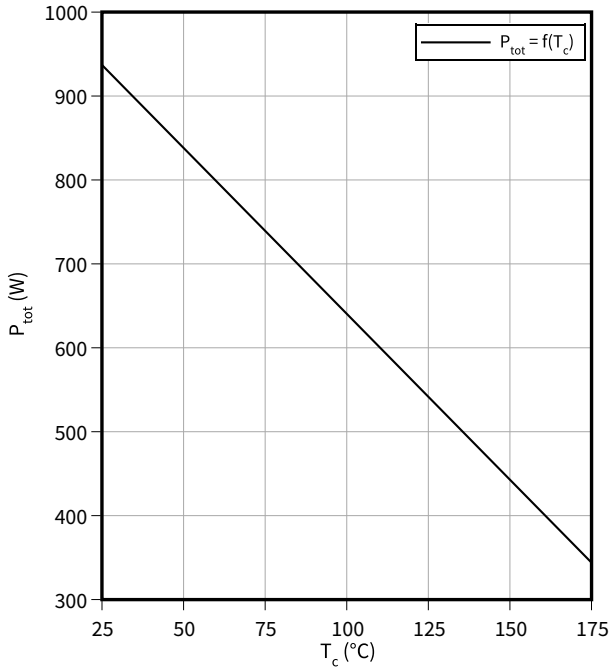
Dynamic test circuit, parasitic inductance $L_\sigma = 50 \text{ nH}$, parasitic capacitor $C_\sigma = 30 \text{ pF}$ from Fig. E. Energy losses include "tail" and diode reverse recovery.

4 Characteristics diagrams

Power dissipation as a function of case temperature

$$P_{tot} = f(T_c)$$

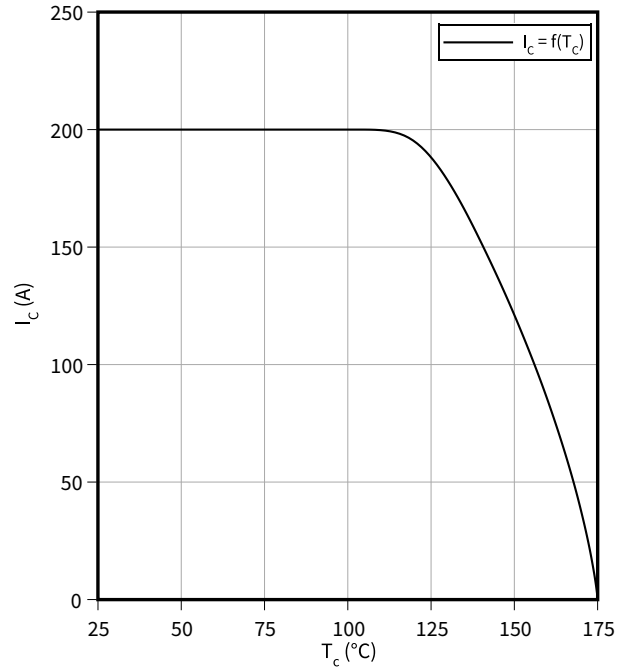
$$T_{vj} \leq 175 \text{ }^\circ\text{C}$$



Collector current as a function of case temperature

$$I_c = f(T_c)$$

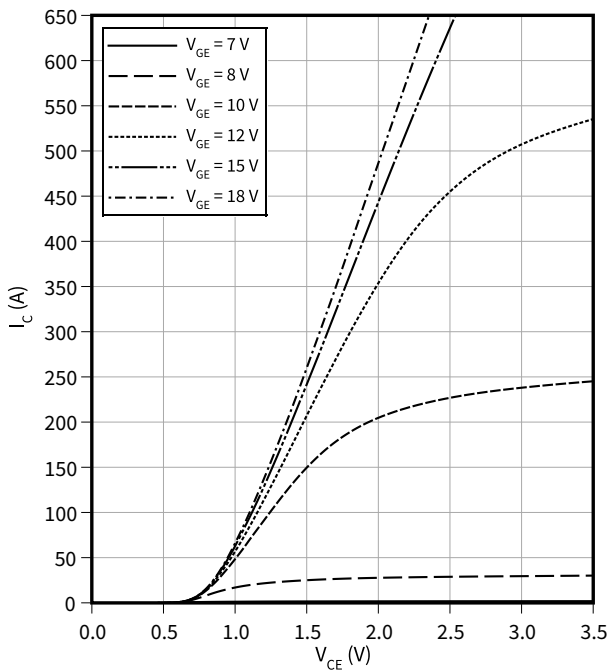
$$T_{vj} \leq 175 \text{ }^\circ\text{C}, V_{GE} = 15 \text{ V}$$



Typical output characteristic

$$I_c = f(V_{CE})$$

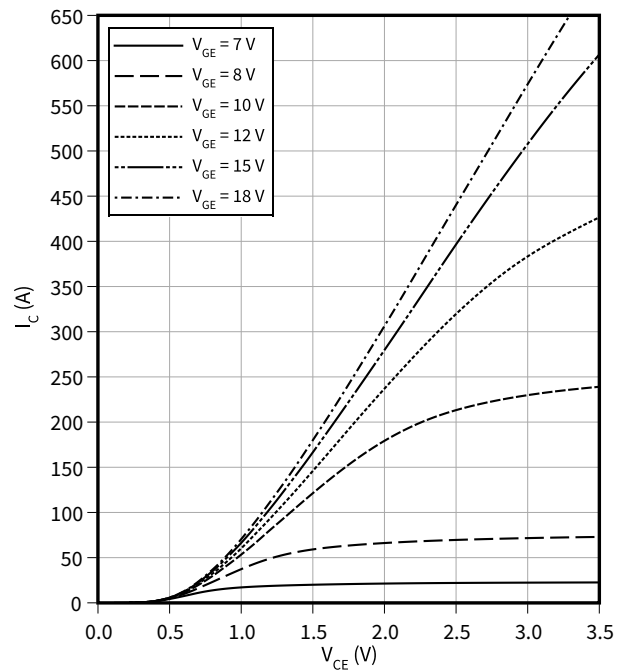
$$T_{vj} = 25 \text{ }^\circ\text{C}$$



Typical output characteristic

$$I_c = f(V_{CE})$$

$$T_{vj} = 175 \text{ }^\circ\text{C}$$

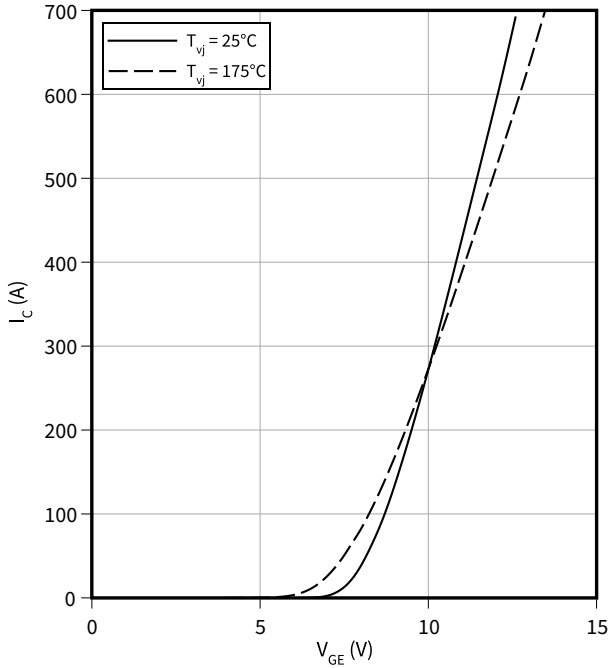


4 Characteristics diagrams

Typical transfer characteristic

$I_C = f(V_{GE})$

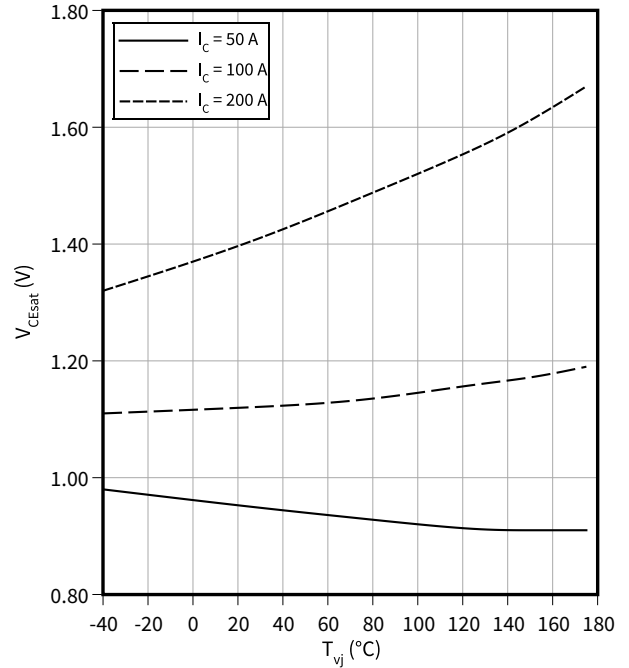
$V_{CE} = 20 \text{ V}$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

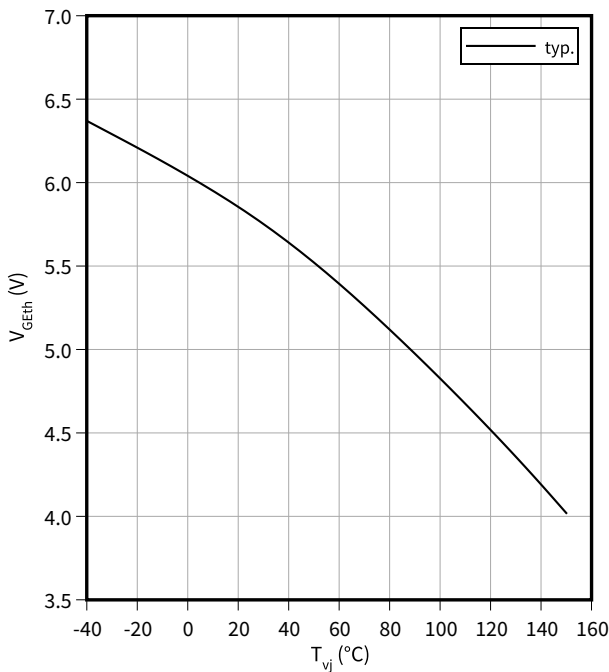
$V_{GE} = 15 \text{ V}$



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

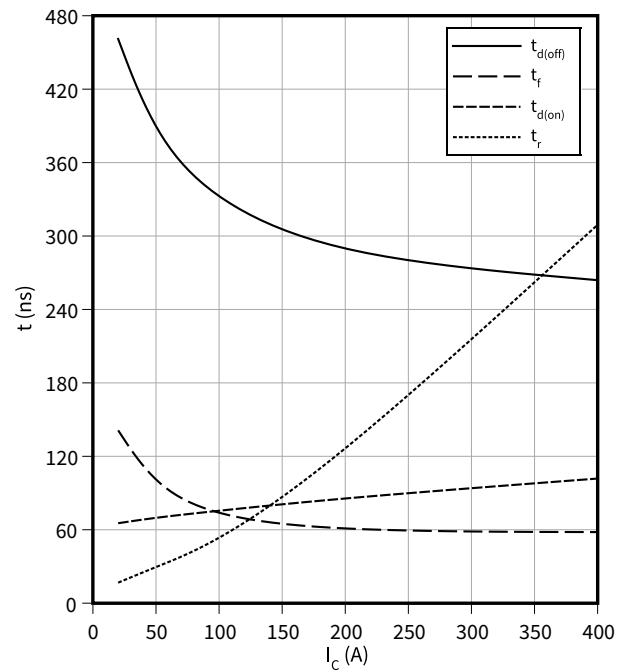
$I_C = 2.6 \text{ mA}$



Typical switching times as a function of collector current

$t = f(I_C)$

$V_{CC} = 470 \text{ V}, T_{vj} = 175^\circ\text{C}, V_{GE} = -8/15 \text{ V}, R_G = 5 \Omega$

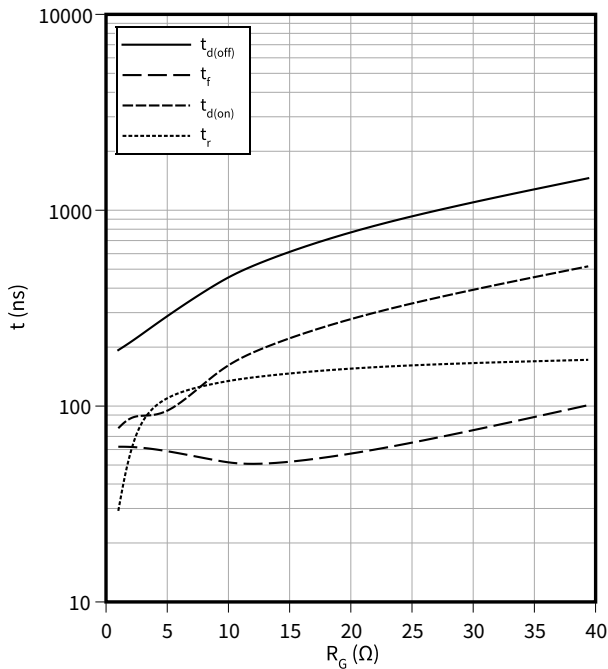


4 Characteristics diagrams

Typical switching times as a function of gate resistor

$t = f(R_G)$

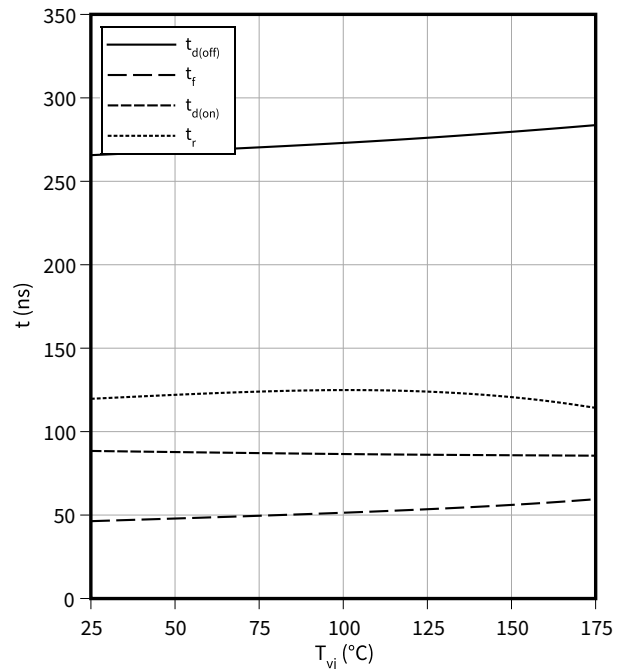
$I_C = 200 \text{ A}, V_{CC} = 470 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = -8/15 \text{ V}$



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

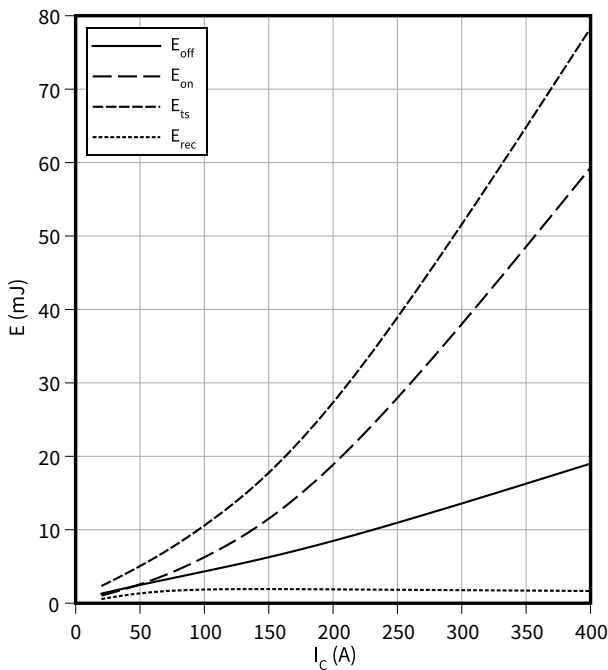
$I_C = 200 \text{ A}, V_{CC} = 470 \text{ V}, V_{GE} = -8/15 \text{ V}, R_G = 5 \text{ } \Omega$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

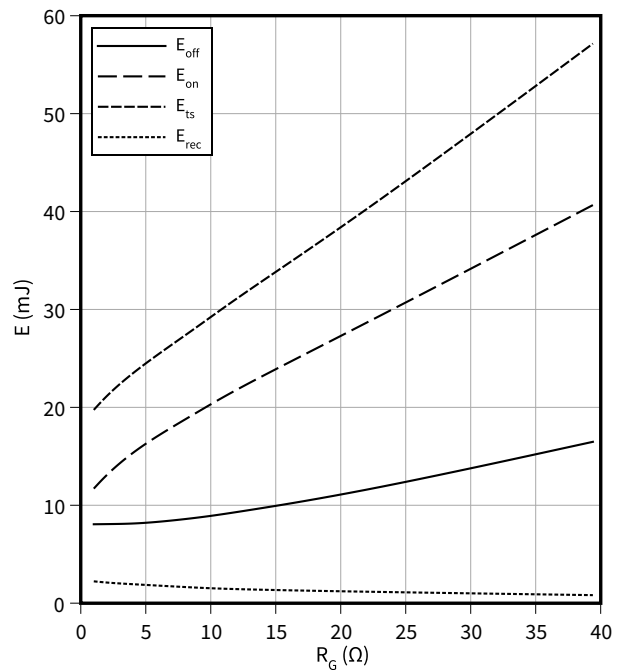
$V_{CC} = 470 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = -8/15 \text{ V}, R_G = 5 \text{ } \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

$I_C = 200 \text{ A}, V_{CC} = 470 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = -8/15 \text{ V}$

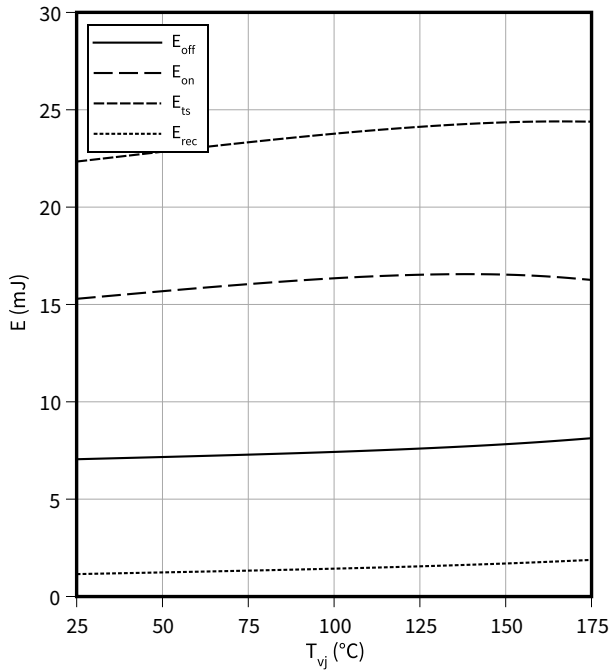


4 Characteristics diagrams

Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

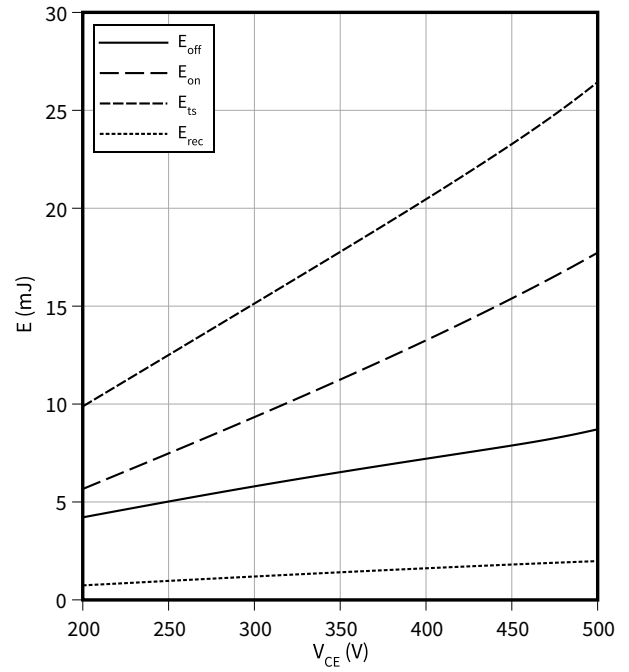
$I_C = 200\text{ A}$, $V_{CC} = 470\text{ V}$, $V_{GE} = -8/15\text{ V}$, $R_G = 5\ \Omega$



Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

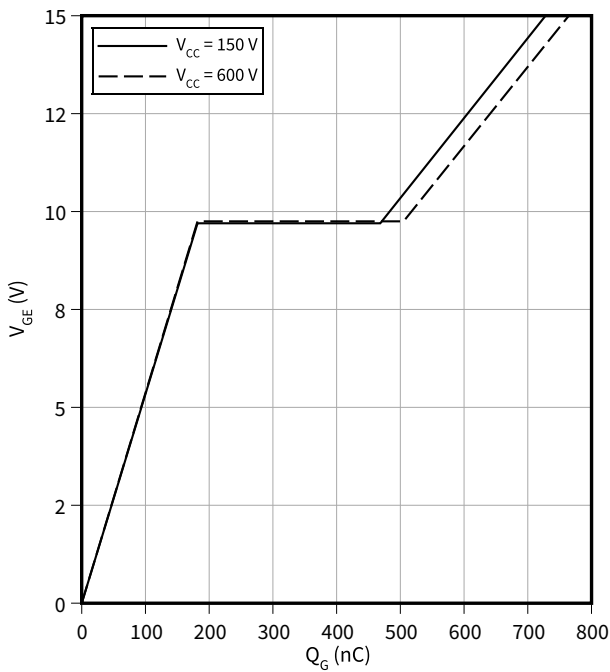
$I_C = 200\text{ A}$, $V_{GE} = -8/15\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_G = 5\ \Omega$



Typical gate charge

$V_{GE} = f(Q_G)$

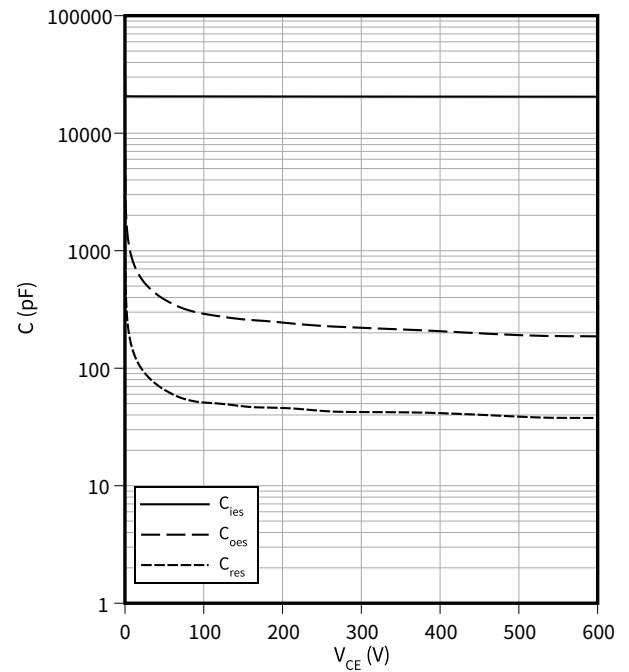
$I_C = 200\text{ A}$



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

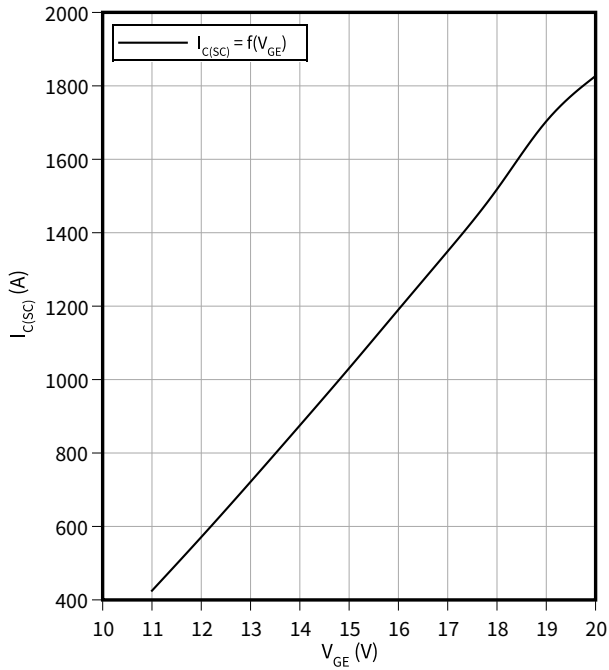
$f = 100\text{ kHz}$, $V_{GE} = 0\text{ V}$



4 Characteristics diagrams

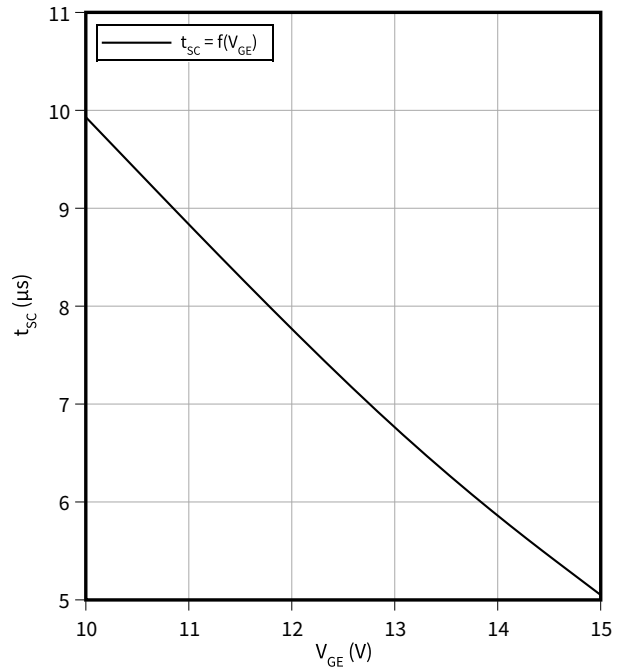
Typical short circuit collector current as a function of gate-emitter voltage

$I_{C(SC)} = f(V_{GE})$
 $T_{vj} \leq 175\text{ }^\circ\text{C}, V_{CC} \leq 470\text{ V}$



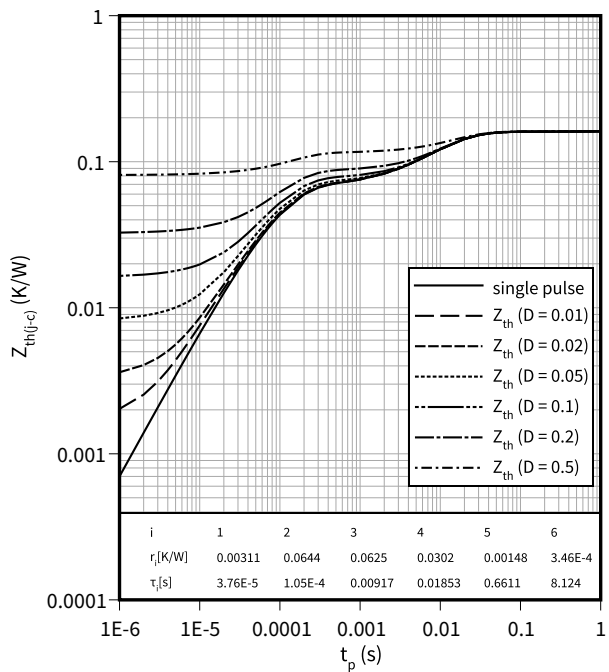
Short circuit withstand time as a function of gate-emitter voltage

$t_{SC} = f(V_{GE})$
 $T_{vj} \leq 175\text{ }^\circ\text{C}, V_{CC} \leq 470\text{ V}$



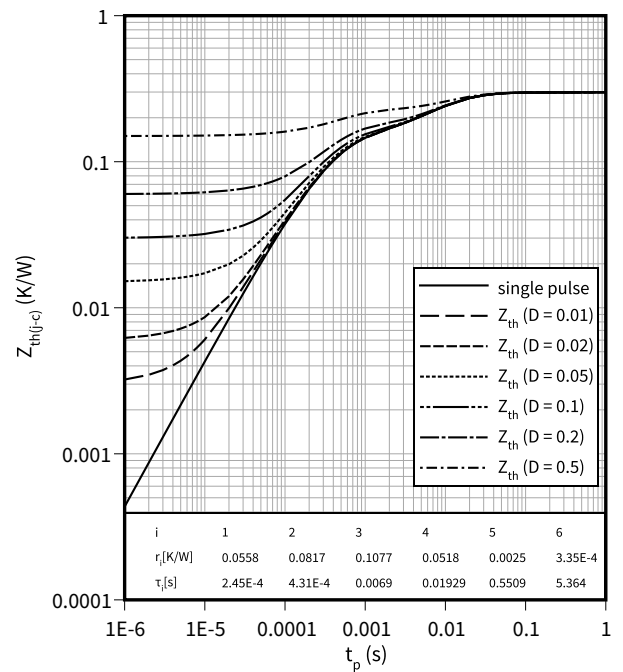
IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



Diode transient thermal impedance as a function of pulse width

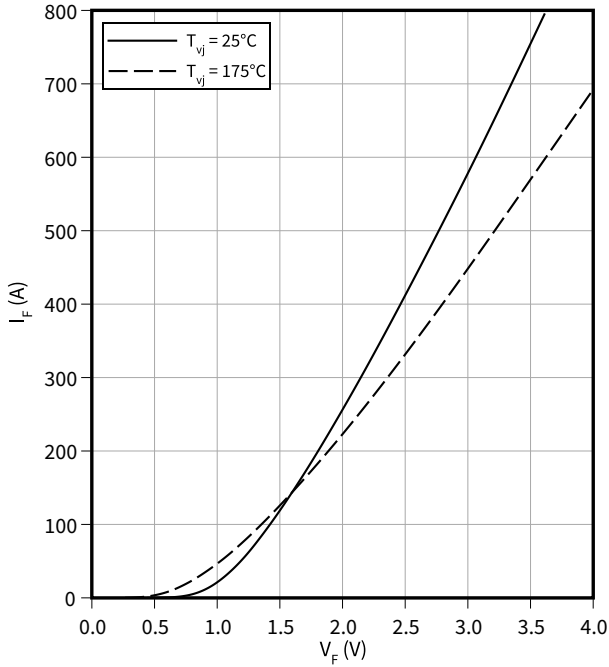
$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



4 Characteristics diagrams

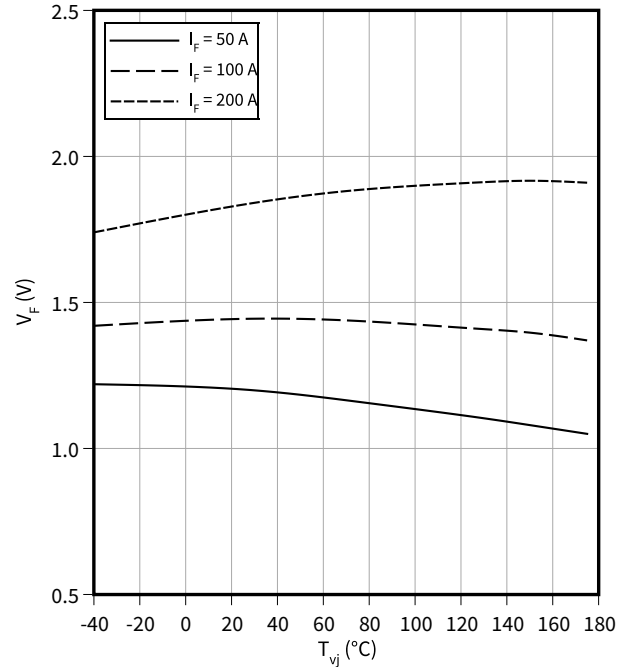
Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature

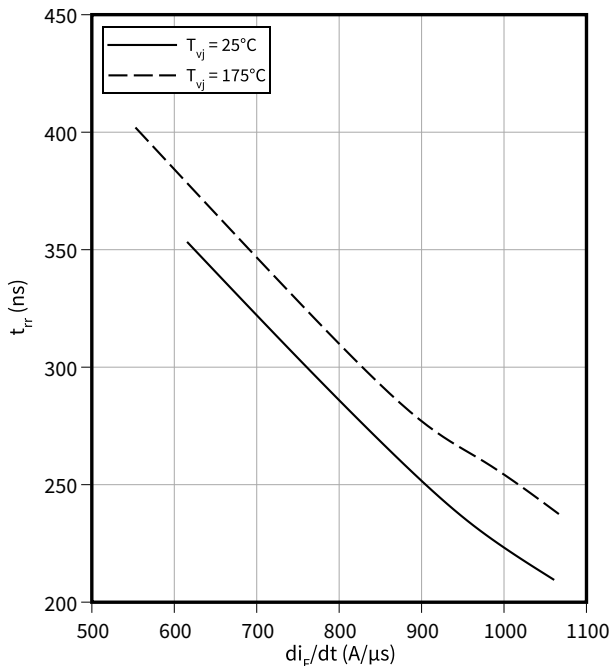
$V_F = f(T_{vj})$



Typical reverse recovery time as a function of diode current slope

$t_{rr} = f(di_F/dt)$

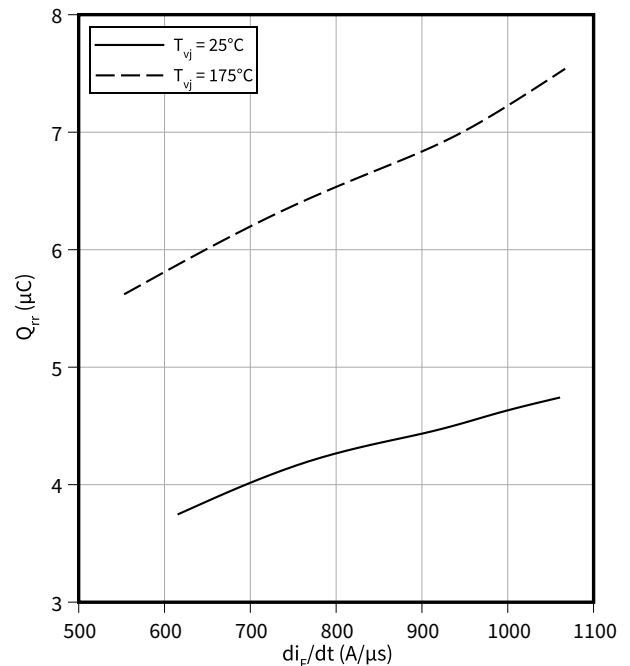
$V_R = 470\text{ V}, I_F = 200\text{ A}$



Typical reverse recovery charge as a function of diode current slope

$Q_{rr} = f(di_F/dt)$

$V_R = 470\text{ V}, I_F = 200\text{ A}$

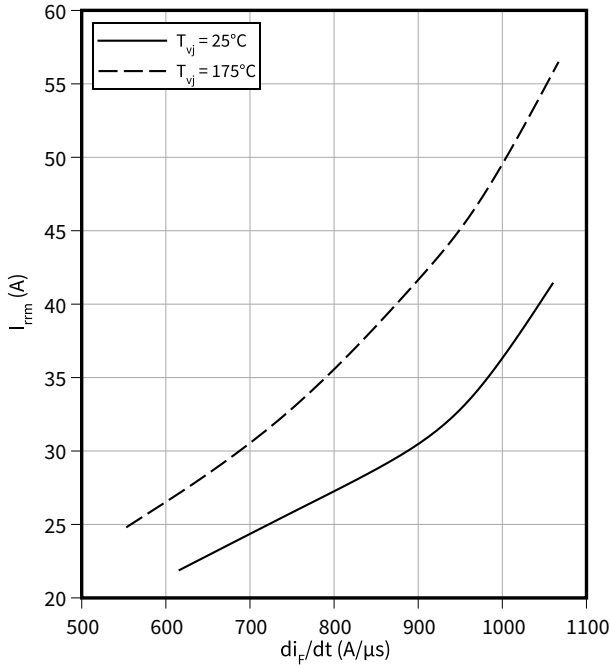


4 Characteristics diagrams

Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

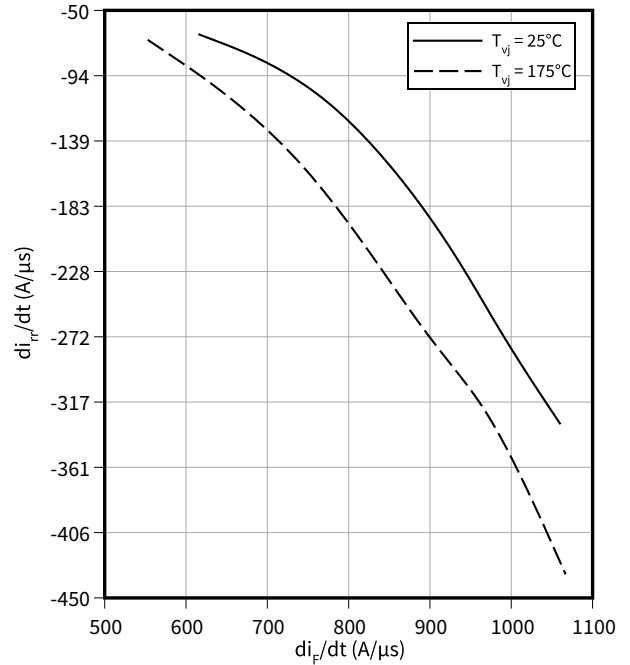
$V_R = 470\text{ V}, I_F = 200\text{ A}$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

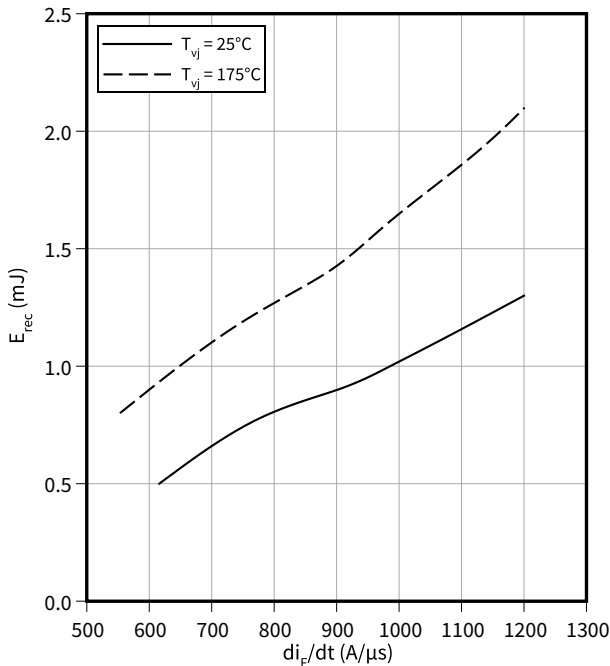
$V_R = 470\text{ V}, I_F = 200\text{ A}$



Typical reverse energy losses as a function of diode current slope

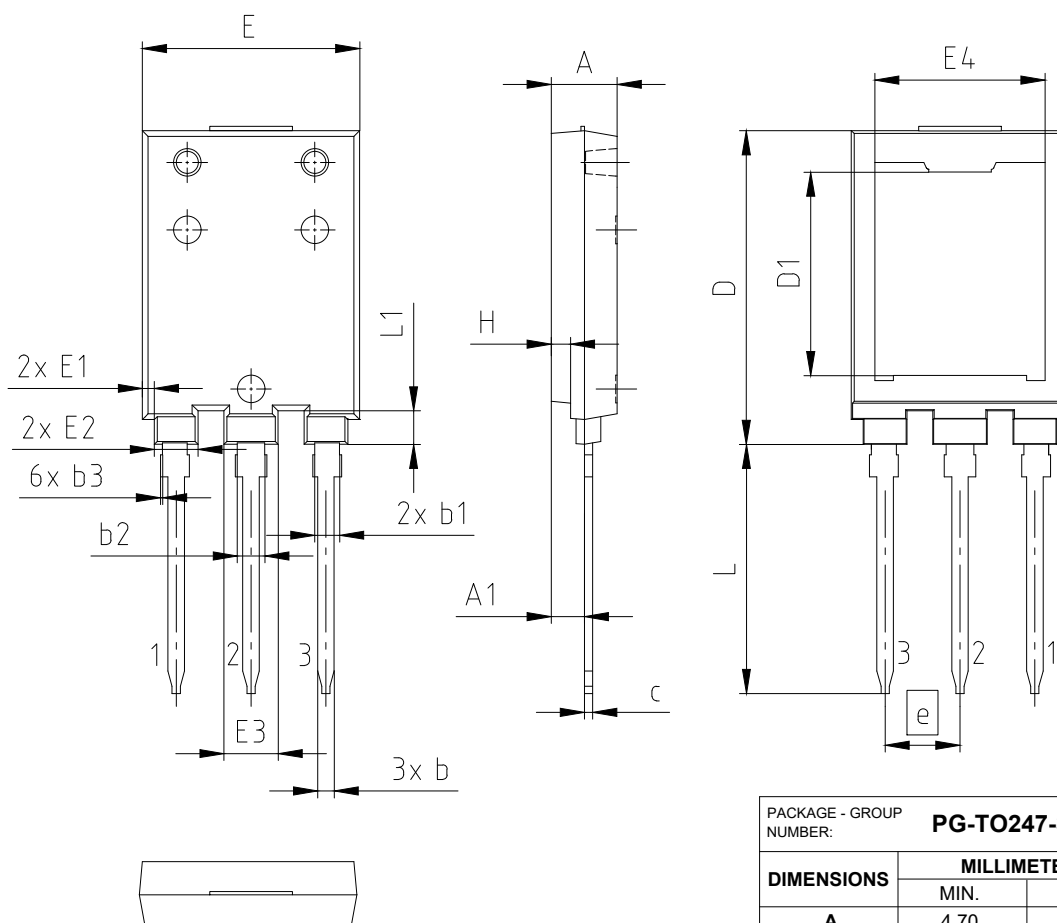
$E_{rec} = f(di_F/dt)$

$V_R = V, I_F = 200\text{ A}$



5 Package outlines

PG-TO247-3-PLUS-NN8.5



PACKAGE - GROUP NUMBER:		PG-TO247-3-U02	
DIMENSIONS	MILLIMETERS		
	MIN.	MAX.	
A	4.70	4.90	
A1	2.16	2.66	
b	1.10	1.30	
b1	1.80		
b2	2.00		
b3	0.00	0.15	
c	0.50	0.70	
D	22.70	22.90	
D1	14.69	14.89	
E	15.70	15.90	
E1	0.76	0.96	
E2	3.08	3.28	
E3	3.84	4.04	
E4	12.28	12.48	
e	5.44		
N	3		
H	1.30	1.50	
L	18.01	18.21	
L1	2.34	2.54	
aaa	0.25		

NOTES:

- (1) ALL METAL SURFACES TIN PLATED EXCEPT AREA OF CUT
- (2) MOLD GATE PROTRUSION AFTER DEGATING.

Figure 1

6 Testing conditions

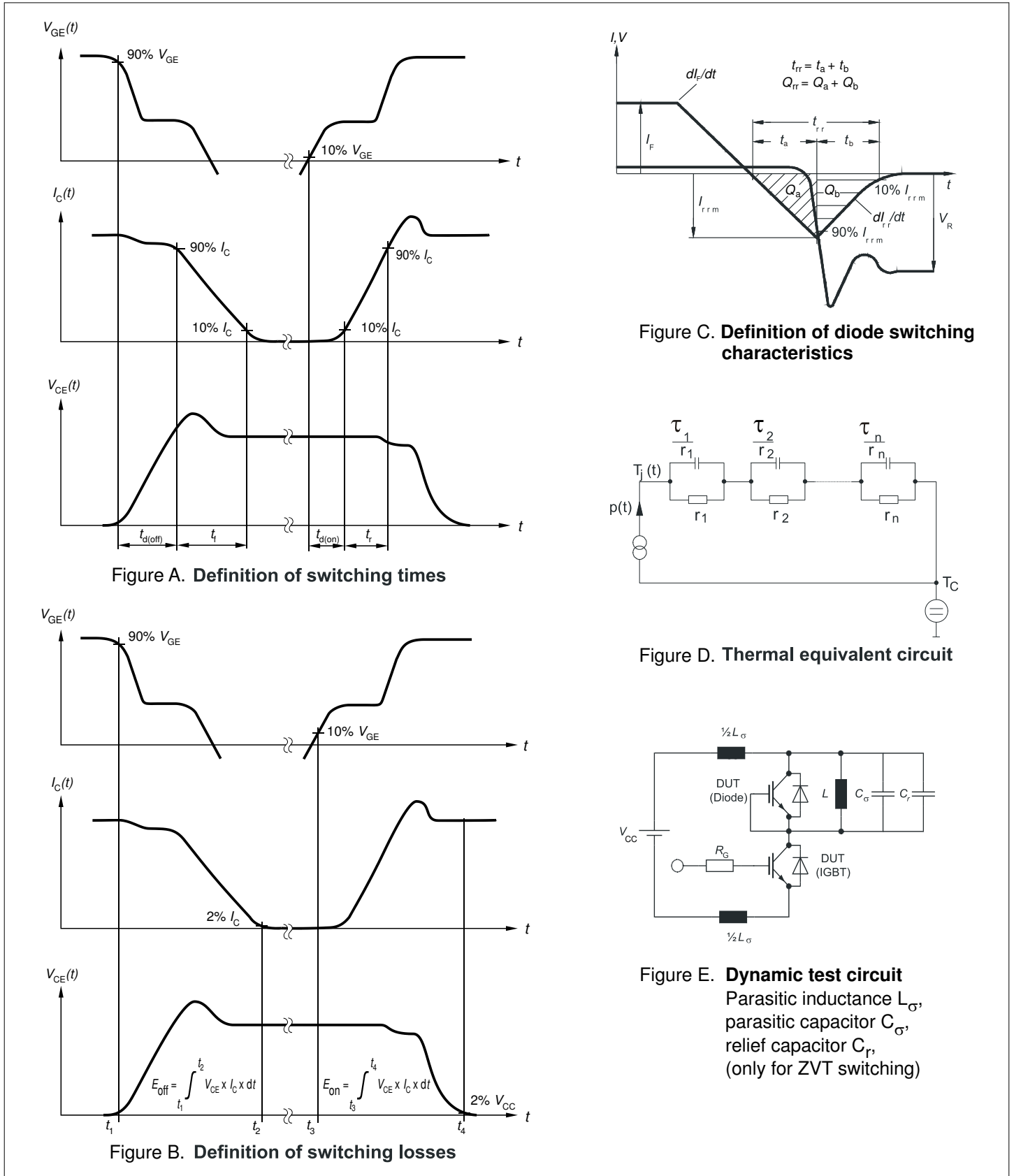


Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2023-02-21	Target datasheet
0.20	2024-02-21	Preliminary datasheet

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